Low Dropout Voltage Tracking Regulator

The NCV4254C is a monolithic integrated low dropout tracking voltage regulator designed to provide an adjustable buffered output voltage that closely tracks the reference input voltage. The output delivers up to 70 mA while being able to be configured higher, lower or equal to the reference voltages.

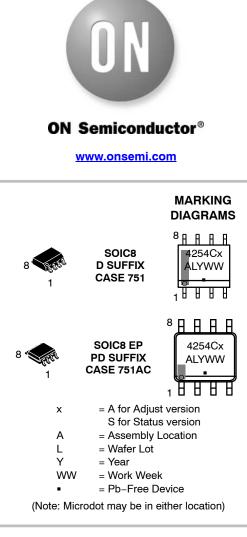
The part can be used in automotive applications with remote sensors or any situation where it is necessary to isolate the output of the other regulator. The NCV4254C also enables the user to bestow a quick upgrade to their module when added current is needed and the existing regulator cannot provide.

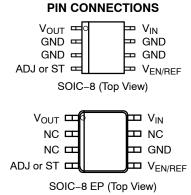
Features

- Up to 70 mA Source Capability
- Low Output Tracking Tolerance
- Low Dropout (typ. 220 mV @ 70 mA)
- Low Disable Current in Stand-by Mode
- Wide Input Voltage Operating Range
- Protection Features:
 - Current Limitation
 - Thermal Shutdown
 - Reverse Input Voltage and Reverse Bias Voltage
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Grade 1 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

• Off the module loads (e.g. sensors power supply)





ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

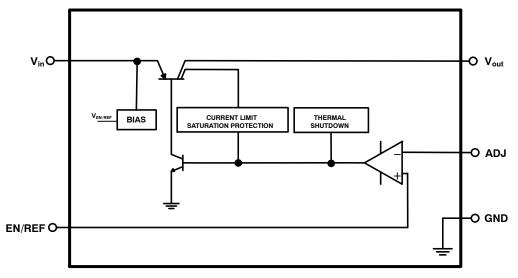


Figure 1. Block Diagram for Adjust Version NCV4254C

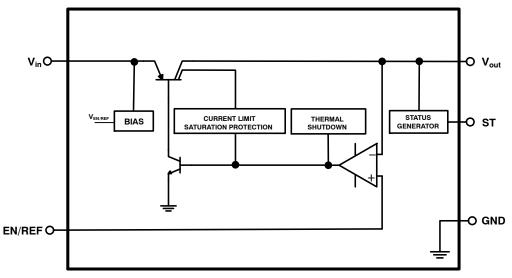


Figure 2. Block Diagram for Status Output for NCV4254C

Table 1. PIN FUNCTION DESCRIPTION

Pin No. SOIC-8	Pin No. SOIC-8 EP	Pin Name	Description
1	1	V _{out}	Tracker Output Voltage. Connect 2.2 μF capacitor with ESR < 5 Ω to ground be connected directly or by a voltage divider for lower output voltages.
2, 3, 6, 7	6	GND	Power Supply Ground.
_	2, 3, 7	NC	Not Connected. Connect to GND
4	4	ADJ	Voltage Adjust Input. The adjust input can be connected directly to output pin for Vout = VEN/REF or by a voltage divider for higher/lower output voltages. The adjust pin can be also connected to ground in case of using this device as a High–Side Driver.
4	4	ST	Tracking Regulator Status Output. Open collector output. Connect via a pull-up resistor to a positive voltage rail. A low signal indicates fault conditions at the regulator's output.
5	5	EN/REF	Enable / Reference. Connect the reference to this pin. A low signal disables the IC; a high signal switches it on. The reference voltage can be connected directly or by a voltage divider for lower output voltages.
8	8	V _{in}	Positive Power Supply Input. Connect 0.1 μ F capacitor to ground.
_	PAD	PAD	Exposed Pad. Connect to GND

Table 2. MAXIMUM RATINGS

Rating		Symbol	Min	Мах	Unit
Input Voltage DC (Note 1)	DC	V _{in}	-20	45	V
Peak Transient Voltage (Load Dump) (Note 2)		V _{in}		45	V
Output Voltage		V _{out}	-5	40	V
Enable / Reference Input Voltage	DC	V_{EN}/REF	-20	40	V
Adjust Voltage (Adjust Version)	DC	V _{ADJ}	-20	40	V
Status output Voltage (Status Output Version)	DC	V _{ST}	-0.3	7	V
Maximum Junction Temperature		T _{J(max)}	-40	150	°C
Storage Temperature		T _{STG}	-55	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

 Load Dump Test B (with centralized load dump suppression) according to ISO16750-2 standard. Guaranteed by design. Not tested in production. Passed Class B according to ISO16750-1.

Table 3. ESD CAPABILITY (Note 3)

Rating	Symbol	Min	Мах	Unit
ESD Capability, Human Body Model	ESD _{HBM}	-4	4	kV

3. This device series incorporates ESD protection and is tested by the following methods:

ESD Human Body Model tested per AEC-Q100-002 (JS-001-2010)

ESD Machine Model tested per AEC-Q100-003 (EIA/JESD22-A115)

Field Induced Charge Device Model ESD characterization is not performed on plastic molded packages with body sizes <50 mm² due to the inability of a small package body to acquire and retain enough charge to meet the minimum CDM discharge current waveform characteristic defined in JEDEC JS-002-2014

Table 4. LEAD SOLDERING TEMPERATURE AND MSL (Note 4)

Rating		Symbol	Min	Мах	Unit
Moisture Sensitivity Level	SOIC-8 SOIC-8 EP	MSL	-	2	-

4. For more information, please refer to our Soldering and Mounting Techniques Reference Manual, SOLDERRM/D

Table 5. THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, SOIC-8 Thermal Resistance, Junction-to-Ambient (Note 5)	$R_{ heta JA}$	115	°C/W
Thermal Reference, Junction-to-Case Top (Note 5) Thermal Characteristics, SOIC-8 EP	R _{ΨJT}	11.5	°C/W
Thermal Resistance, Junction-to-Ambient (Note 5) Thermal Reference, Junction-to-Case Top (Note 5)	R _{θJA} R _{ΨJT}	75 11.5	

5. Values based on copper area of 645 mm² (or 1 in²) of 1 oz copper thickness and FR4 PCB substrate.

Table 6. RECOMMENDED OPERATING RANGES

Rating	Symbol	Min	Мах	Unit
Input Voltage	V _{in}	4	45	V
Enable / Reference Input Voltage	V _{EN/REF}	2	-	V
Junction Temperature	TJ	-40	150	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 7. ELECTRICAL CHARACTERISTICS V_{in} = 13.5 V, $V_{EN/REF}$ >= 2.5 V, C_{in} = 0.1 μ F, C_{out} = 2.2 μ F, for typical values T_J = 25°C, for min/max values T_J = -40°C to 150°C; unless otherwise noted. (Note 6)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
REGULATOR OUTPUT	•					
Output Voltage Tracking Accuracy	V_{in} = 5.7 V to 26 V, I_{out} = 0.1 mA to 60 mA 2.5 V \leq $V_{EN/REF} \leq$ (V_IN $-$ 600 mV)	ΔV_{out}	-3	-	3	mV
Output Voltage Tracking Accuracy	$V_{in} = 5.5 \text{ V}$ to 26 V, $I_{out} = 0.1 \text{ mA}$ to 60 mA VEN/REF = 5 V		-10	-	10	mV
Output Voltage Tracking Accuracy	V_{in} = 5.5 V to 32 V, I_{out} = 0.1 mA to 30 mA $V_{EN/REF}$ = 5 V	ΔV_{out}	-10	-	10	mV
Line Regulation	V_{in} = 5.5 V to 32 V, I_{out} = 5 mA, $V_{EN/REF}$ = 5 V	Reg _{line}	-5	-	5	mV
Load Regulation	I_{out} = 0.1 mA to 70 mA, $V_{EN/REF}$ = 5 V	Reg _{load}	-5	-	5	mV
Dropout Voltage (Note 7)	$I_{out} = 70 \text{ mA}, V_{EN/REF} = 5 \text{ V}$	V _{DO}	-	220	400	mV
DISABLE AND QUIESCENT CURRENTS						
Disable Current, Stand-by Mode	$V_{EN/REF} \leq 0.4 \ V, \ T_J \leq 125^{\circ}C$	I _{DIS}	-	0.01	5	μA
Quiescent Current, $I_q = I_{in} - I_{out}$	$I_{out} \le 0.1 \text{ mA}, V_{EN/REF} = 5 \text{ V}$ $I_{out} \le 70 \text{ mA}, V_{EN/REF} = 5 \text{ V}$	Ιq	-	65 1	80 2	μA mA
CURRENT LIMIT PROTECTION	•					
Current Limit	$V_{out} = (V_{EN/REF} - 0.1 \text{ V}), V_{EN/REF} = 5 \text{ V}$	I _{LIM}	71	110	150	mA
REVERSE CURRENT PROTECTION						
Reverse Current	$V_{in} = 0 \text{ V}, V_{out} = 32 \text{ V}, V_{EN/REF} = 5 \text{ V}$	I _{out_rev}	-15	-10	-	mA
Reverse Current at Negative Input Voltage	$V_{in} = -16$ V, $V_{out} = 0$ V, $V_{EN/REF} = 5$ V	l _{in_rev}	-1	-0.2	-	mA
PSRR				-		-
Power Supply Ripple Rejection (Note 8)	f = 100 Hz, 1 V _{p-p}	PSRR	-	60	-	dB
ENABLE / REFERENCE						
Enable / Reference Input Threshold Voltage Logic Low Logic High	V_{out} = 0 V, I_{out} \leq 5 μ A, Tj \leq 125°C $ V_{out} - V_{EN/REF} $ < 10 mV	V _{th(EN/R} EF)	- 2		0.4	V
Logic High	$ v_{out} - v_{EN/REF} < 10 \text{ mV}$		2	-	-	

6. Performance guaranteed over the indicated operating temperature range by design and/or characterization tested at T_A ≈ T_J. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 7. Measured when output voltage falls 100 mV below the regulated voltage at Vin = 13.5 V.

8. Values based on design and/or characterization.

Table 7. ELECTRICAL CHARACTERISTICS V _{in} = 13.5 V, V _{EN/REF} >= 2.5 V, C _{in} = 0.1 μF, C _{out} = 2.2 μF, for typical values T _J =	
25°C, for min/max values $T_J = -40$ °C to 150°C; unless otherwise noted. (Note 6)	

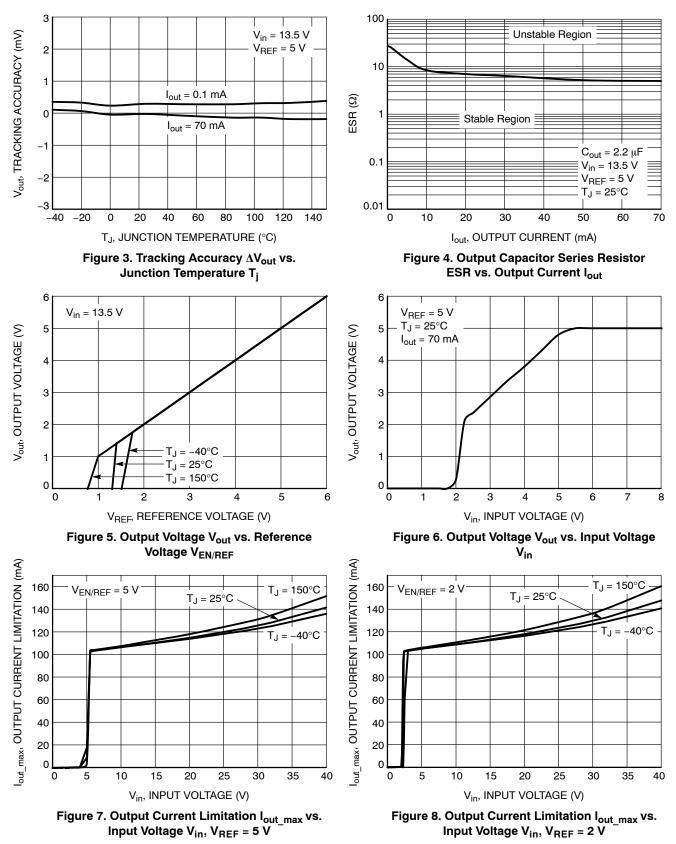
Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
ENABLE / REFERENCE	•					
Enable / Reference Input Current	V _{EN/REF} = 5 V	I _{EN/REF}	-	2	3	μA
Enable / Reference Input Current if Input tied to GND	V_{in} = 0 V, $V_{EN/REF}$ = 5 V	I _{EN/REF}	-	0.003	0.6	mA
Enable / Reference Internal Pull-Down Resistor		R _{EN/REF}	1.7	2.2	3.3	MΩ
ADJUST (only Adjust Version)						
Adjust Input Biasing Current	V _{ADJ} = 5 V	I _{ADJ}	-	0.03	0.5	μA
STATUS OUTPUT (only Status Version)	·		-			
Status Switching Threshold, Undervoltage	V _{out} decreasing	V _{out_UV}	V _{EN/REF} –120	V _{EN/REF} -77	V _{EN/REF} -50	mV
Status Switching Threshold, Overvoltage	V _{out} increasing	V _{out_OV}	V _{EN/REF} +50	V _{EN/REF} +77	V _{EN/REF} +120	mV
Status reaction Time		t _{ST}	10	23	33	μs
Status Output Low Voltage	I_{ST} = 1 mA, $V_{in} \ge$ 4 V	V _{ST_low}	_	-	0.4	V
Status Output Sink Current Limitation	V _{ST} = 0.8 V	I _{ST_max}	1	-	-	mA
Status Output Leakage Current	V _{out} = V _{EN/REF} , V _{ST} = 5 V	I _{ST_leak}	-	-	2	μA
THERMAL SHUTDOWN		•	-			
Thermal Shutdown Temperature (Note 8)		T _{SD}	151	175	200	°C

6. Performance guaranteed over the indicated operating temperature range by design and/or characterization tested at $T_A \approx T_J$. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 7. Measured when output voltage falls 100 mV below the regulated voltage at Vin = 13.5 V.

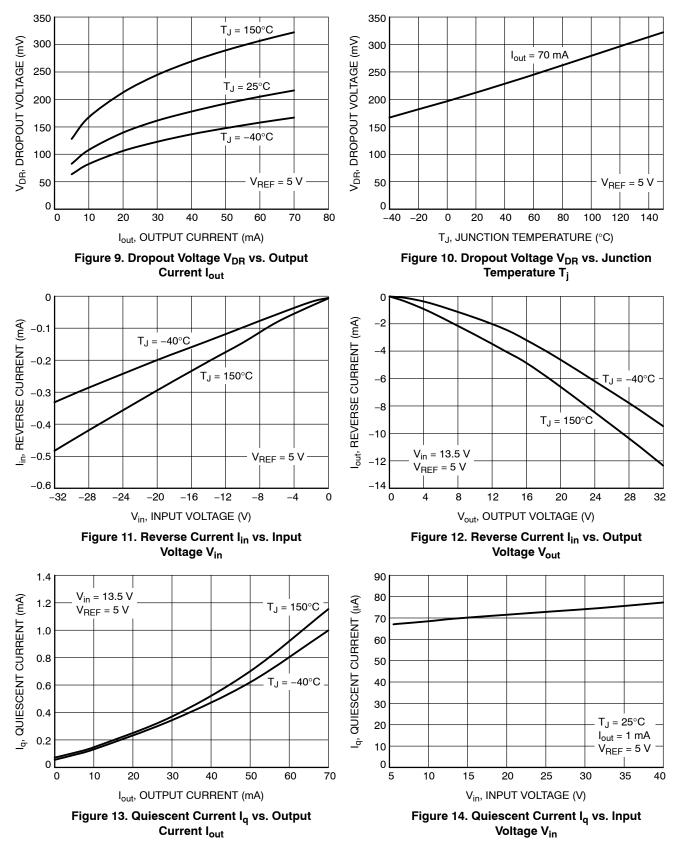
8. Values based on design and/or characterization.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.





TYPICAL CHARACTERISTICS





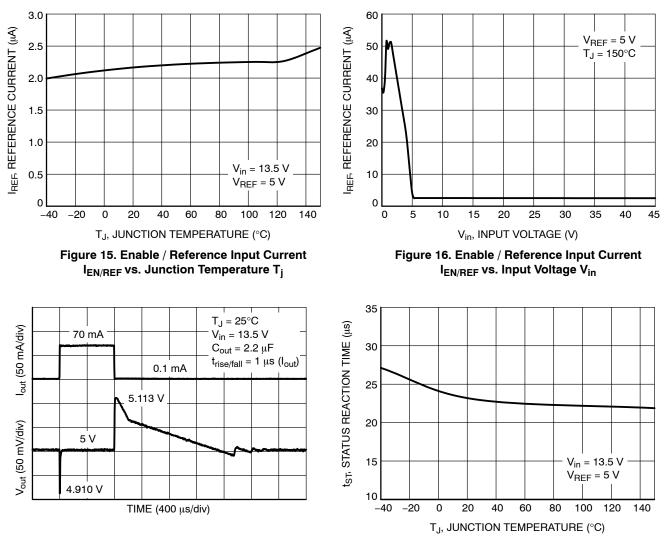


Figure 17. Load Transient

Figure 18. Status Reaction Time t_{ST} vs. Junction Temperature T_J

APPLICATION INFORMATION

The NCV4254C tracking regulator is self-protected with internal thermal shutdown and internal current limit. Typical characteristics are shown in Figure 3 to Figure 18.

Input Decoupling (Cin)

A ceramic or tantalum 0.1 μ F capacitor is recommended and should be connected close to the NCV4254C package. Higher capacitance and lower ESR will improve the overall line and load transient response.

If extremely fast input voltage transients are expected then appropriate input filter must be used in order to decrease rising and/or falling edges below 50 V/ μ s for proper operation. The filter can be composed of several capacitors in parallel.

Output Decoupling (Cout)

The output capacitor for the NCV4254C is required for stability. Without it, the regulator output will oscillate. Actual size and type may vary depending upon the application load and temperature range. Capacitor effective series resistance (ESR) is also a factor in the IC stability. Worst-case is determined at the minimum ambient temperature and maximum load expected.

The output capacitor can be increased in size to any desired value above the minimum. One possible purpose of this would be to maintain the output voltage during brief conditions of negative input transients that might be characteristic of a particular system.

The capacitor must also be rated at all ambient temperatures expected in the system. To maintain regulator stability down to -40° C, a capacitor rated at that temperature must be used.

Tracking Regulator

The output voltage V_{out} is controlled by comparing it to the voltage applied at pin EN/REF and driving a PNP pass transistor accordingly. The control loop stability depends on the output capacitor C_{out} , the load current, the chip temperature and the poles/zeros introduced by the integrated circuit.

Protection circuitry prevents the IC as well as the application from destruction in case of catastrophic events. These safeguards contain output current limitation, reverse polarity protection as well as thermal shutdown in case of over temperature.

In order to avoid excessive power dissipation that could never be handled by the pass element and the package, the maximum output current is decreased at high input voltages.

The over temperature protection circuit prevents the IC from immediate destruction under fault conditions (e.g. Output continuously short–circuited) by reducing the output current. A thermal balance below 200°C junction temperature is established. Please note that a junction

temperature above 150°C is outside the maximum ratings and reduces the IC lifetime.

The NCV4254C allows a negative supply voltage. However, several small currents are flowing into the IC. For details see electrical characteristics table and typical performance graphs. The thermal protection circuit is not operating during reverse polarity condition.

Thermal Considerations

As power in the NCV4254C increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part. When the NCV4254C has good thermal conductivity through the PCB, the junction temperature will be relatively low with high power applications. The maximum dissipation the NCV4254C can handle is given by:

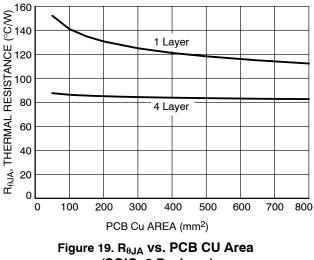
$$\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = \frac{\left[\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}\right]}{\mathsf{R}_{\mathsf{\theta}\mathsf{J}\mathsf{A}}} \tag{eq. 1}$$

Since T_J is not recommended to exceed 150°C, then the NCV4254C (SOIC–8 EP) soldered on 645 mm², 1 oz copper area, FR4 can dissipate up to 1.667 W when the ambient temperature (T_A) is 25°C. See Figure 19 and 20 for $R_{\theta JA}$ versus PCB Cu area. The power dissipated by the NCV4254C can be calculated from the following equations:

$$\mathsf{P}_{\mathsf{D}} \approx \mathsf{V}_{\mathsf{in}} \big(\mathsf{I}_{\mathsf{q}} @ \mathsf{I}_{\mathsf{out}} \big) + \mathsf{I}_{\mathsf{out}} \big(\mathsf{V}_{\mathsf{in}} - \mathsf{V}_{\mathsf{out}} \big) \qquad (\mathsf{eq. 2})$$

or

$$V_{in(MAX)} \approx rac{\mathsf{P}_{\mathsf{D}(MAX)} + (\mathsf{V}_{out} \times \mathsf{I}_{out})}{\mathsf{I}_{out} + \mathsf{I}_{q}}$$
 (eq. 3)



(SOIC–8 Package)

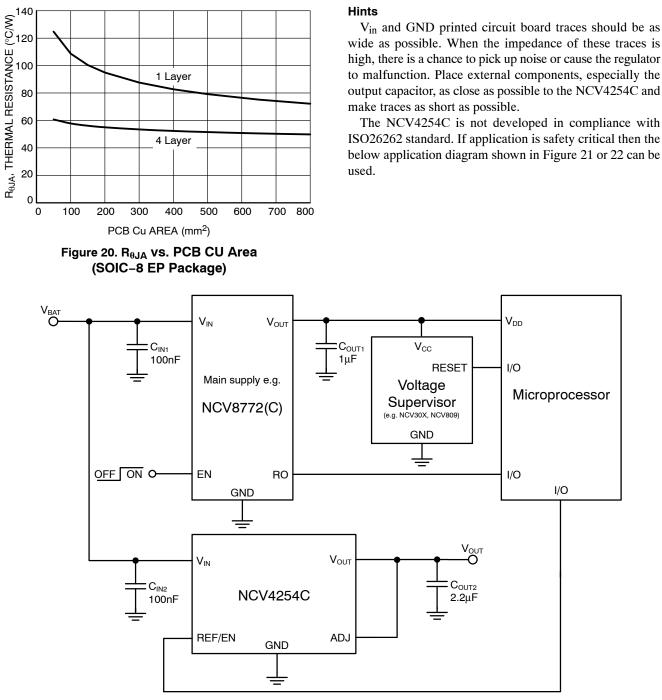


Figure 21. Application Diagram for ADJ version

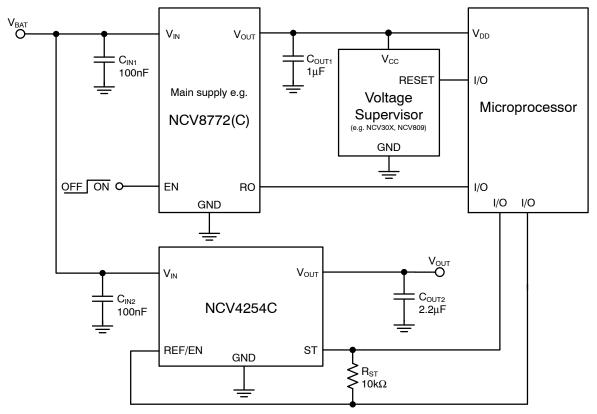


Figure 22. Application Diagram for ST version

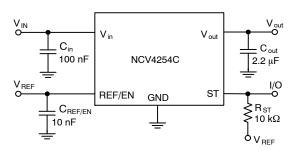
CIRCUIT DESCRIPTION

ENABLE Function

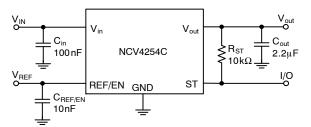
By pulling the $V_{REF/EN}$ lead below 0.4 V typically, the IC is disabled and enters a Stand–by mode where the device draws less then 5 μA from supply. When the $V_{REF/EN}$ lead is greater then 1.75 V, V_{OUT} tracks the $V_{REF/EN}$ lead normally.

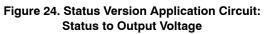
STATUS Output

The status output is used as the power on indicator to the microcontroller. This signal indicates when the output voltage is suitable for reliable operation of the sensor. It pulls low when the output is not considered to be ready. ST is pulled up to V_{REF} (Figure 23) or V_{out} (Figure 24) by an external resistor, typically 10 k Ω .









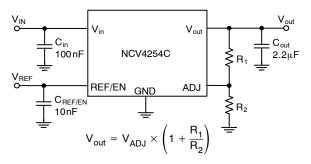


Figure 25. Adjust Version Application Circuit: Output Voltage Higher Than the Reference Voltage

Output Voltage

The output is capable of supplying 70 mA to the load while configured as a similar (Figure 26), lower (Figure 27) or higher (Figure 25) voltage as the reference lead. The Adj lead acts as the inverting terminal of the op amp and the V_{REF} lead as the non-inverting.

The device can also be configured as a high–side driver as displayed in Figure 28.

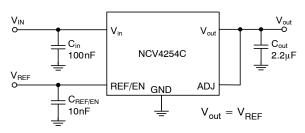


Figure 26. Adjust Version Application Circuit: Output Voltage Equal to the Reference Voltage

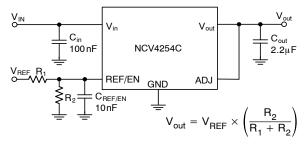


Figure 27. Adjust Version Application Circuit: Output Voltage Lower Than the Reference Voltage

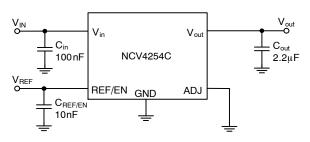


Figure 28. Adjust Version Application Circuit: High–Side Driver

ORDERING INFORMATION

Device	Version	Package	Shipping [†]
NCV4254CDAJR2G	ADJ	SOIC-8	2500 / Tape & Reel
NCV4254CDSTR2G	ST	(Pb-Free)	
NCV4254CPDAJR2G	ADJ	SOIC-8 EP	2500 / Tape & Reel
NCV4254CPDSTR2G	ST	(Pb-Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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the right to make changes without furth purpose, nor does onsemi assume ar	er notice to any products herein. onsemi make ny liability arising out of the application or use	LLC dba onsemi or its subsidiaries in the United States and/or other courses no warranty, representation or guarantee regarding the suitability of its proof any product or circuit, and specifically disclaims any and all liability, incle e under its patent rights nor the rights of others.	oducts for any particular		

SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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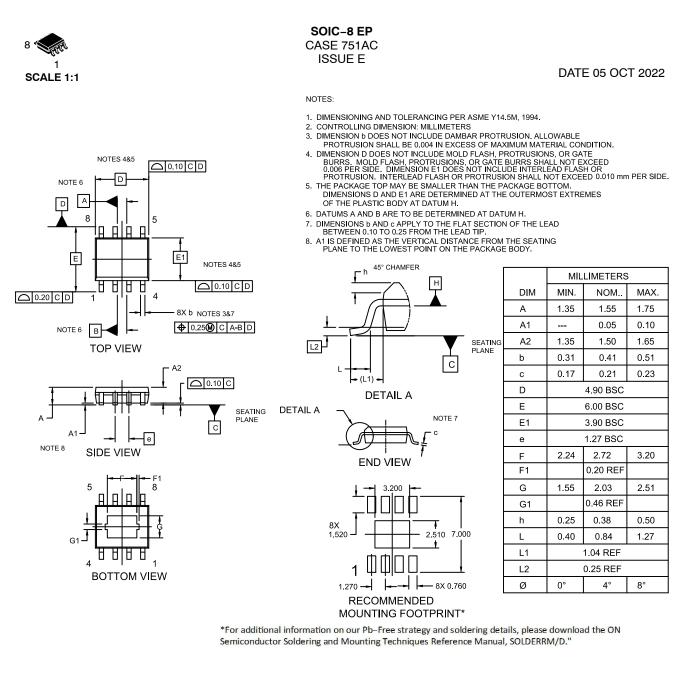
8

COLLECTOR, #1

COLLECTOR, #1

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

DUSEM



GENERIC **MARKING DIAGRAM***

A<u>A</u>B XXXXX AYWW=

XXXXXX	= Specific Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " -", may or may not be present and may be in either location. Some products may not follow the Generic Marking.

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